

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 (TO-220AB) plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{j(max)} = 150\text{ °C}$).

2. Features and benefits

- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- Very high current surge capability
- Planar passivated for voltage ruggedness and reliability
- High turn-on current rise $dI_T/dt = 100\text{ A/}\mu\text{s}$
- High noise immunity $dV_P/dt = 500\text{ V/}\mu\text{s}$ up to 150 °C
- High thermal cycling performance
- High voltage capability

3. Applications

- Ignition circuits
- Protection circuits e.g. SMPS inrush current
- Motor control circuits and starters
- Voltage regulation
- Solid state relays
- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)

4. Quick reference data

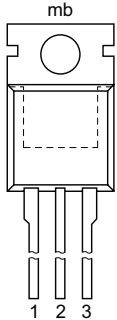

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
Absolute maximum rating				
V_{DRM}	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 128\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	40	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	450	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$	495	A
T_j	junction temperature		150	°C

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ °C}$; Fig. 7		-	-	15	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ °C}$; Fig. 9		-	-	60	mA
V_T	on-state voltage	$I_T = 80\text{ A}$; $T_J = 25\text{ °C}$; Fig. 10		-	-	1.6	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_J = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		500	-	-	V/ μ s

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
3	G	gate		
mb	A	mounting base; connect to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
TYN40-800T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
V_{RRM}	repetitive peak reverse voltage		800	V
$I_{\text{T(AV)}}$	average on-state current	half sine wave; $T_{\text{mb}} \leq 128^{\circ}\text{C}$;	25	A
$I_{\text{T(RMS)}}$	RMS on-state current	half sine wave; $T_{\text{mb}} \leq 128^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	40	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{\text{j(init)}} = 25^{\circ}\text{C}$; $t_{\text{p}} = 10\text{ ms}$; Fig. 4 ; Fig. 5	450	A
		half sine wave; $T_{\text{j(init)}} = 25^{\circ}\text{C}$; $t_{\text{p}} = 8.3\text{ ms}$	495	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ms}$; sine wave	1012.5	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{G}} = 30\text{mA}$	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		5	A
V_{GM}	peak gate voltage		5	V
P_{GM}	peak gate power		20	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	0.5	W
T_{stg}	storage temperature		-40 to 150	$^{\circ}\text{C}$
T_{j}	junction temperature		150	$^{\circ}\text{C}$

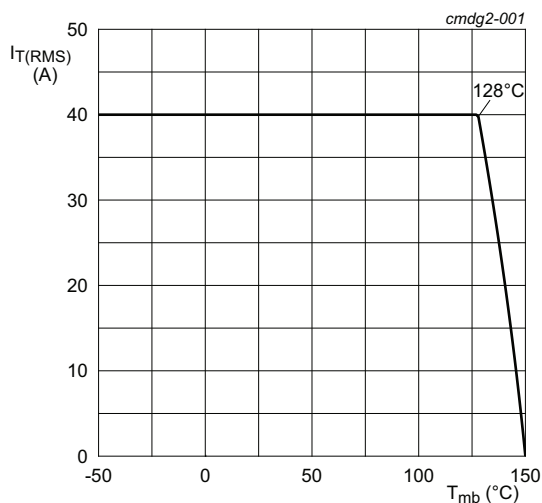


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

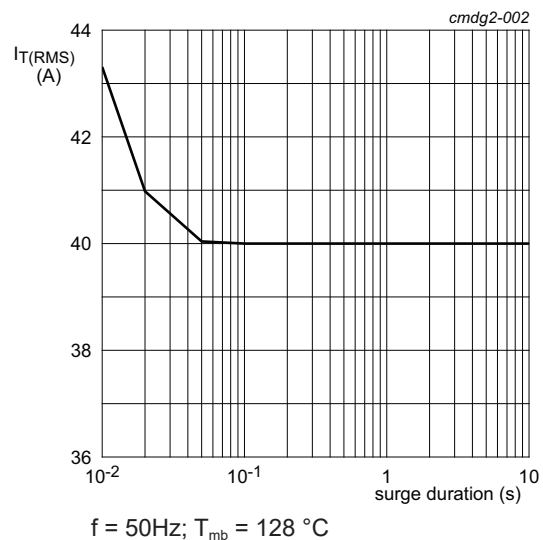


Fig. 2. RMS on-state current as a function of surge duration; maximum values

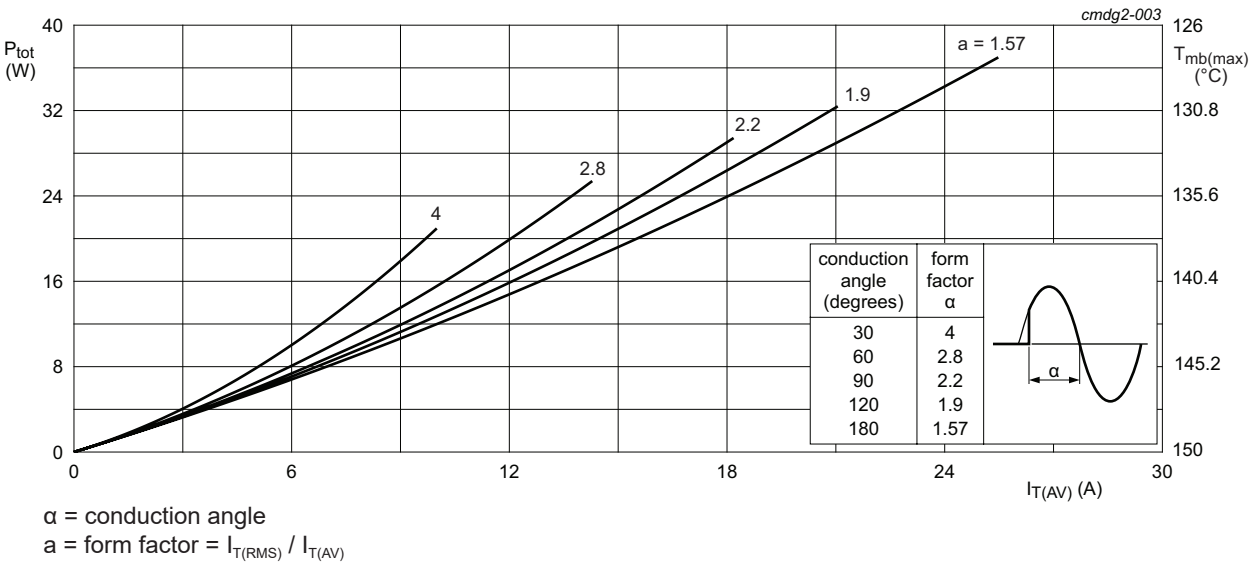


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

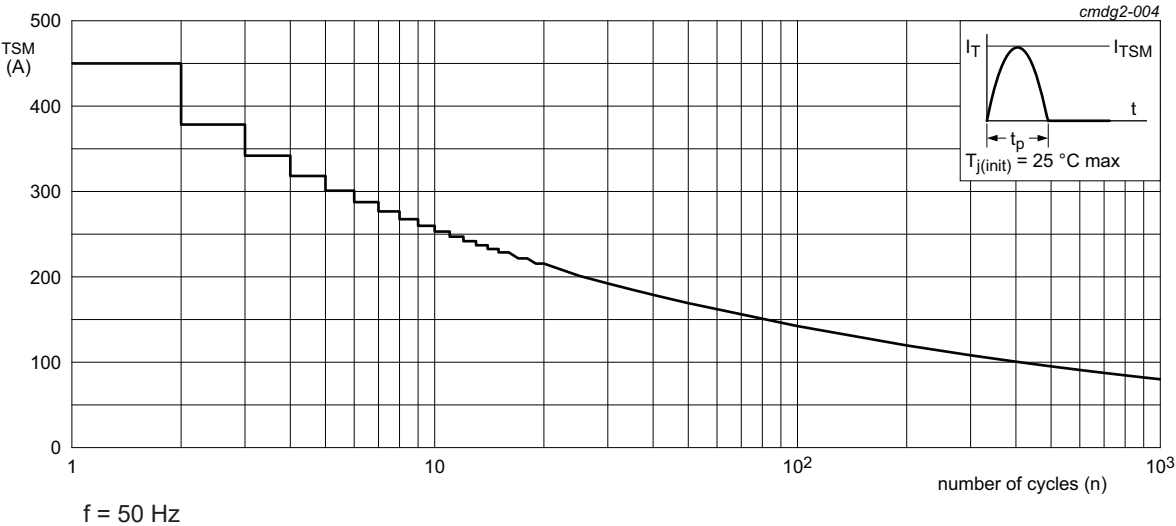


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

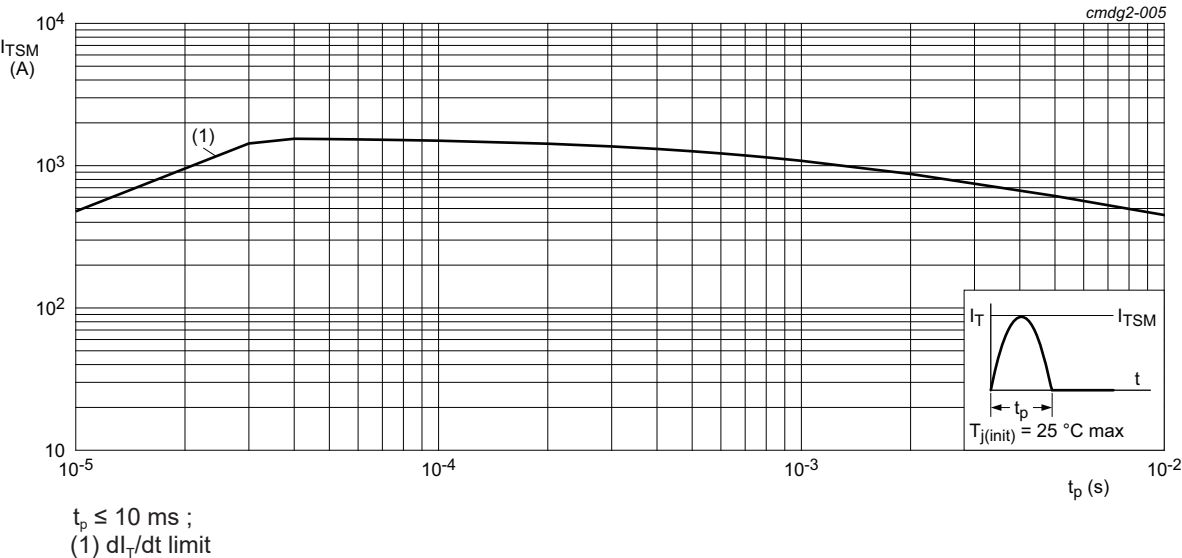


Fig. 5. Total power dissipation as a function of RMS on-state current; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6		-	-	0.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

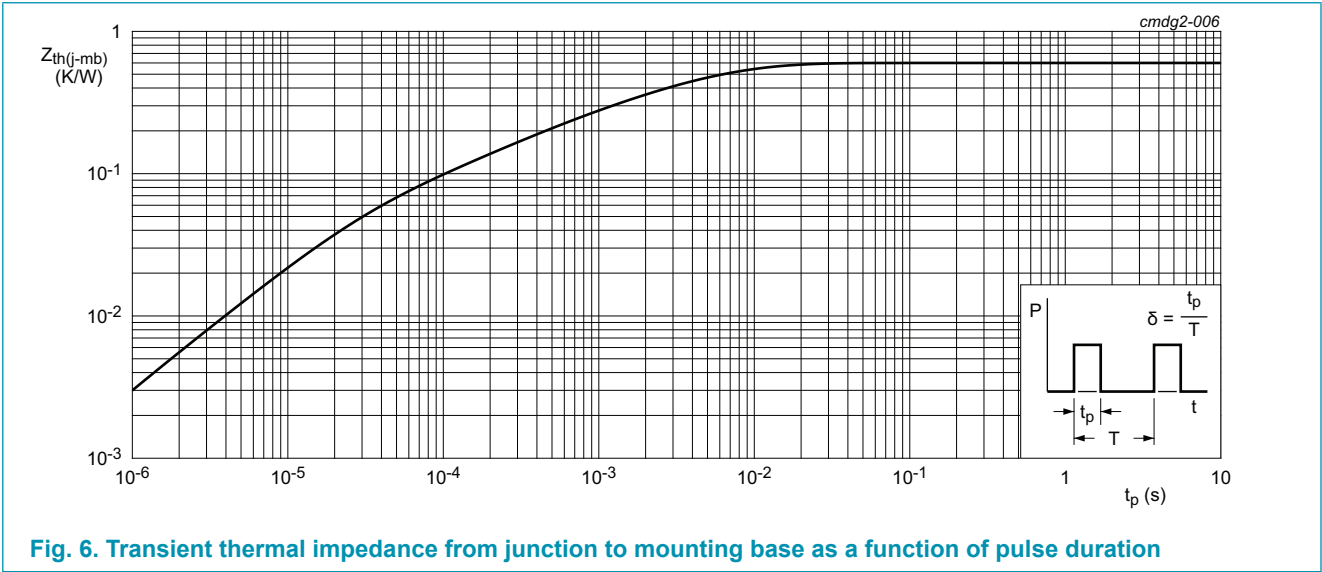


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	-	15	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	-	80	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		-	-	60	mA
V_T	on-state voltage	$I_T = 80\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	-	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 11		-	0.7	1.2	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 150\text{ }^\circ\text{C}$; Fig. 11		0.25	0.5	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_J = 150\text{ }^\circ\text{C}$		-	-	2	mA
I_R	reverse current	$V_D = 800\text{ V}$; $T_J = 150\text{ }^\circ\text{C}$		-	-	2	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_J = 150\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		500	-	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 80\text{ A}$; $V_D = 800\text{ V}$; $I_G = 100\text{ mA}$; $(dI_G/dt)_M = 0.2\text{ A}/\mu\text{s}$; $T_J = 25\text{ }^\circ\text{C}$			2	-	μs
t_q	commutated turn-off time	$V_{DM} = 536\text{ V}$; $T_J = 150\text{ }^\circ\text{C}$; $I_{TM} = 40\text{ A}$; $V_R = 25\text{ V}$; $dV_D/dt = 50\text{ V}/\mu\text{s}$; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$; ($V_{DM} = 67\%$ of V_{DRM})			70	-	μs

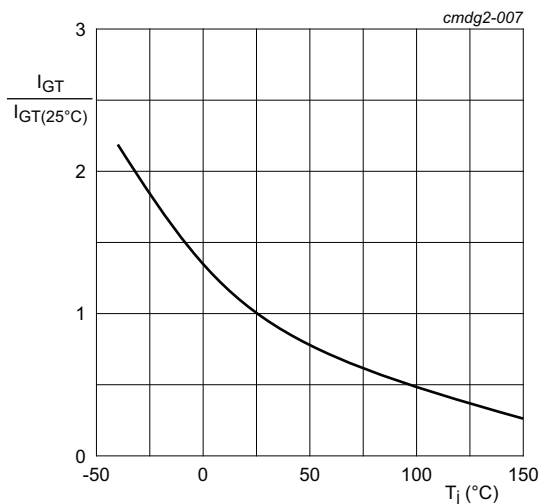


Fig. 7. Normalized gate trigger current as a function of junction temperature

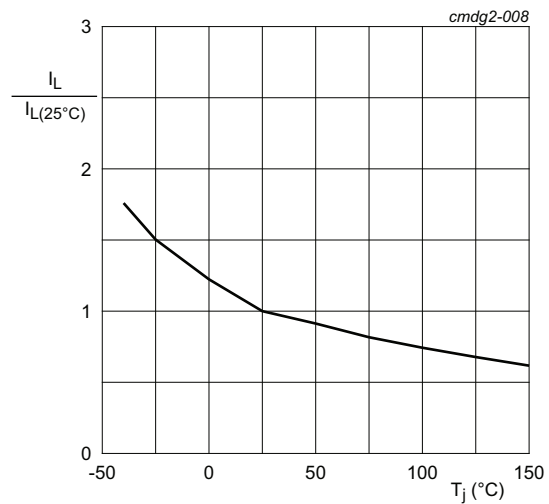


Fig. 8. Normalized latching current as a function of junction temperature

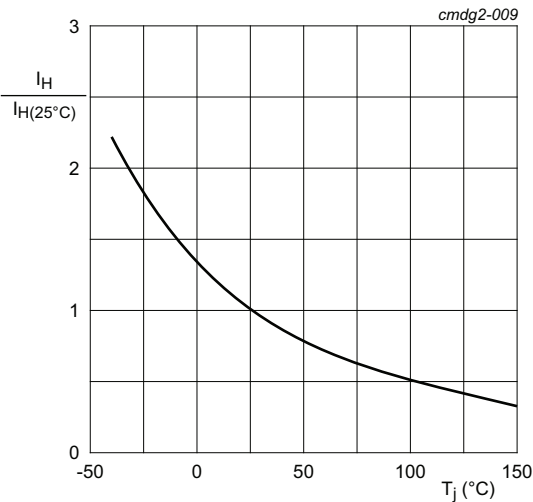
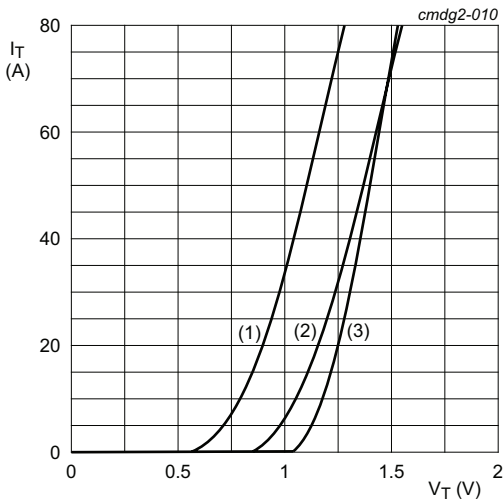


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.036\text{ V}$; $R_s = 0.0066\ \Omega$
(1) $T_J = 150^\circ\text{C}$; typical values
(2) $T_J = 150^\circ\text{C}$; maximum values
(3) $T_J = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

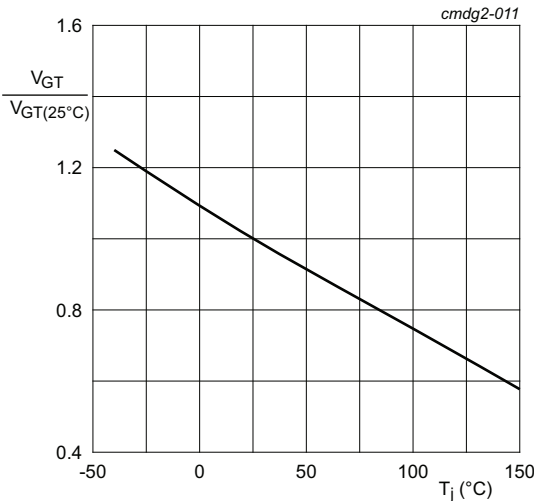
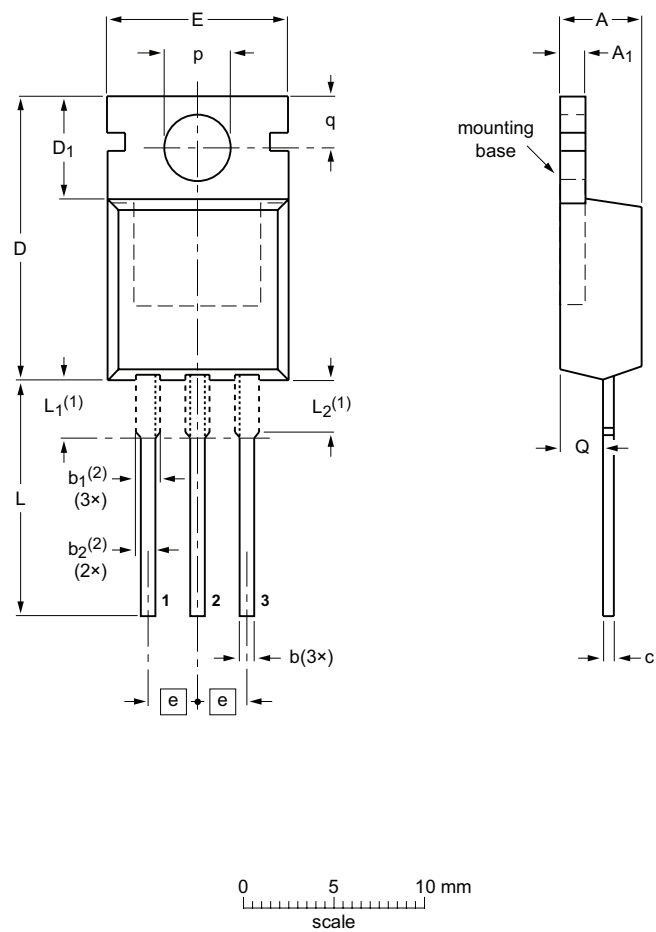


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (²)	b ₂ (²)	c	D	D ₁	E	e	L	L ₁ (¹)	L ₂ (¹) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- Notes
- 1. Lead shoulder designs may vary.
 - 2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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